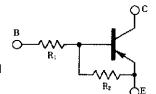


# COMPOUND TRANSISTOR AN1L3N

# on-chip resistor PNP silicon epitaxial transistor For mid-speed switching

#### **FEATURES**

• On-chip bias resistor  $(R_1 = 4.7 \; k\Omega, \; R_2 = 10 \; k\Omega)$ 



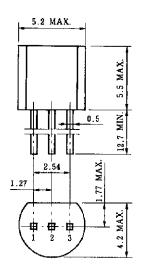
· Complementary transistor with AA1L3N

# ABSOLUTE MAXIMUM RATINGS (Ta = 25°C)

Parameter	Symbol	Ratings	Unit
Collector to base voltage	Vcво	-60	V
Collector to emitter voltage	VCEO	<b>–50</b>	٧
Emitter to base voltage	VEBO	<b>-</b> 5	٧
Collector current (DC)	Ic(DC)	-100	mA
Collector current (Pulse)	Ic(pulse) *	-200	mA
Total power dissipation	Рт	250	mW
Junction temperature	Tj	150	°C
Storage temperature	T <sub>stg</sub>	-55 to +150	°C

<sup>\*</sup> PW  $\leq$  10 ms, duty cycle  $\leq$  50 %

#### PACKAGE DRAWING (UNIT: mm)



#### Electrode Connection

1. Emitter EIAJ : SC -43B
2. Collector JEDEC : TO −92
3. Base IEC : PA33

### **ELECTRICAL CHARACTERISTICS (Ta = 25°C)**

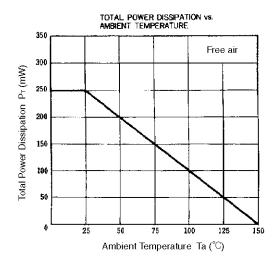
Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Collector cutoff current	Ісво	Vcb = -50 V, IE = 0			-100	nA
DC current gain	h <sub>FE1</sub> **	$V_{CE} = -5.0 \text{ V}, \text{ Ic} = -5.0 \text{ mA}$	35	60	100	-
DC current gain	hFE2 **	VcE = -5.0 V, Ic = -50 mA	80	200		-
Collector saturation voltage	VCE(sat) **	Ic = -5.0  mA, IB = -0.25  mA		-0.04	-0.2	V
Low level input voltage	VIL **	$V_{CE} = -5.0 \text{ V}, \text{ Ic} = -100 \ \mu\text{A}$		-0.9	-0.6	V
High level input voltage	V <sub>IH</sub> **	$V_{CE} = -0.2 \text{ V}, \text{ Ic} = -5.0 \text{ mA}$	-3.0	-1.5		V
Input resistance	R <sub>1</sub>		3.29	4.7	6.11	kΩ
E-to-B resistance	R <sub>2</sub>		7	10	13	kΩ
Turn-on time	ton	$Vcc = -5 \text{ V}, \text{ R}_L = 1 \text{ k}\Omega$			0.2	μs
Storage time	<b>t</b> stg	V <sub>I</sub> = -5 V, PW = 2 μs			5.0	μs
Turn-off time	toff	duty cycle≤2 %			6.0	μs

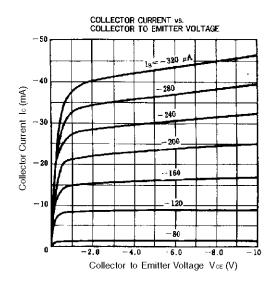
<sup>\*\*</sup> PW  $\leq$  350  $\mu$ s, duty cycle  $\leq$  2 %

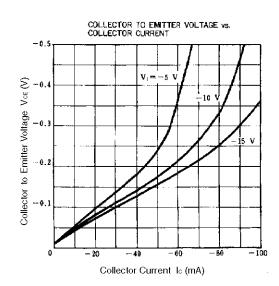
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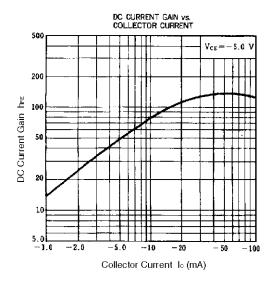


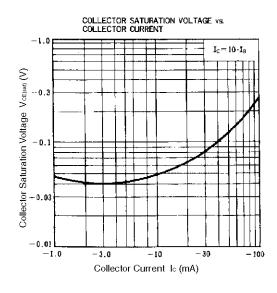
# TYPICAL CHARACTERISTICS (Ta = 25°C)

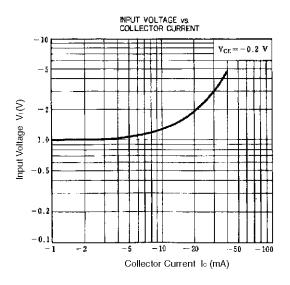


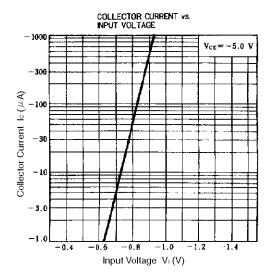


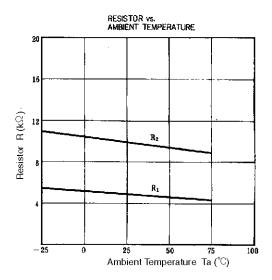












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